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# Advanced Manufacturing of Solid Oxide Electrodes Using ALD

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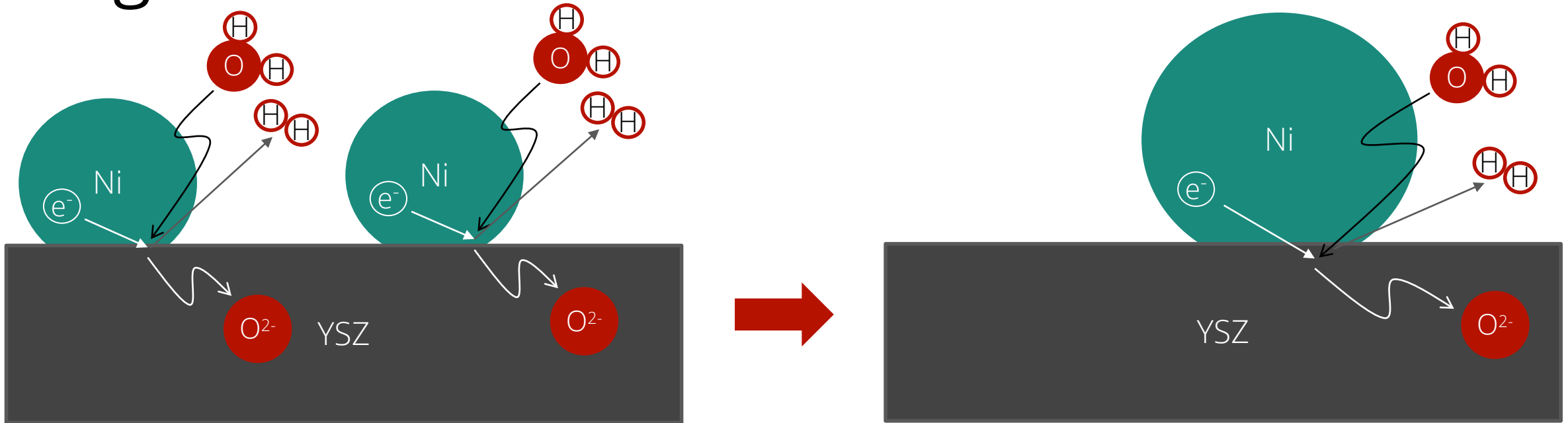
U.S. DOE Office of Fossil Energy and Carbon Management  
DOE SBIR Grant #: DE-SC0022769

RMD Inc. and UPenn and OxEon Energy  
Collaborators: Prof. John Vohs – UPenn  
Dr. Jenna Pike – OxEon Energy

# About RMD

- Founded in 1974
- RMD's mission has been to conduct world-class research and develop industry-leading commercial products.
- More than 60 scientists and engineers
- RMD has a growing portfolio of ALD technologies
  - Microelectronic Semiconductor Coatings
  - Gas Barrier Coatings
  - Anti-Corrosion Coatings
  - X-ray and Neutron Supermirror Coatings

# Hydrogen Electrode Degradation – Nickel Migration



- As Nickel migrates and agglomerates, density of TPBs is reduced

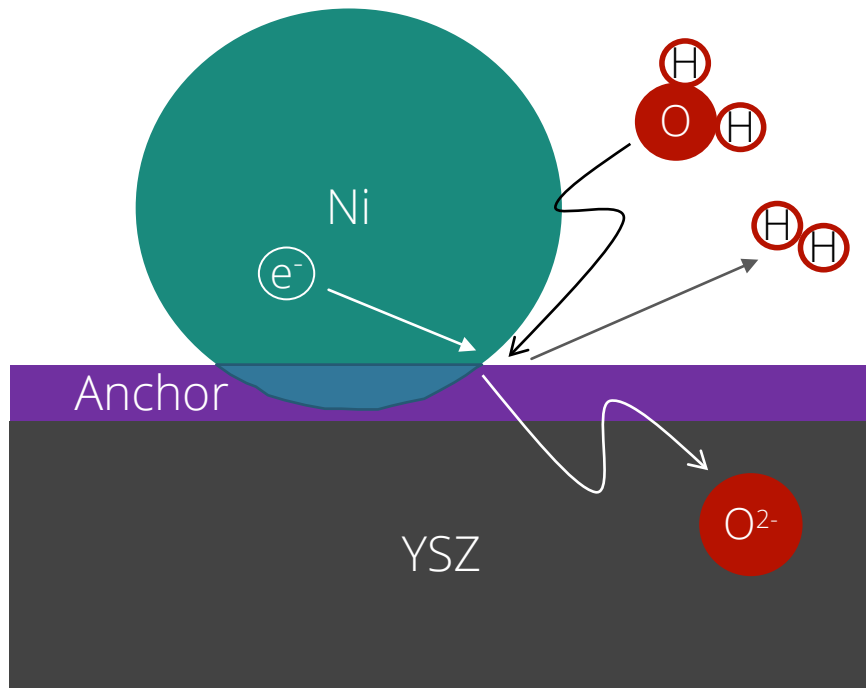
# What's Been Done to Prevent Degradation

- Increasing surface area/density of active TPBs with additional catalysts via infiltration, ALD, PLD, etc.

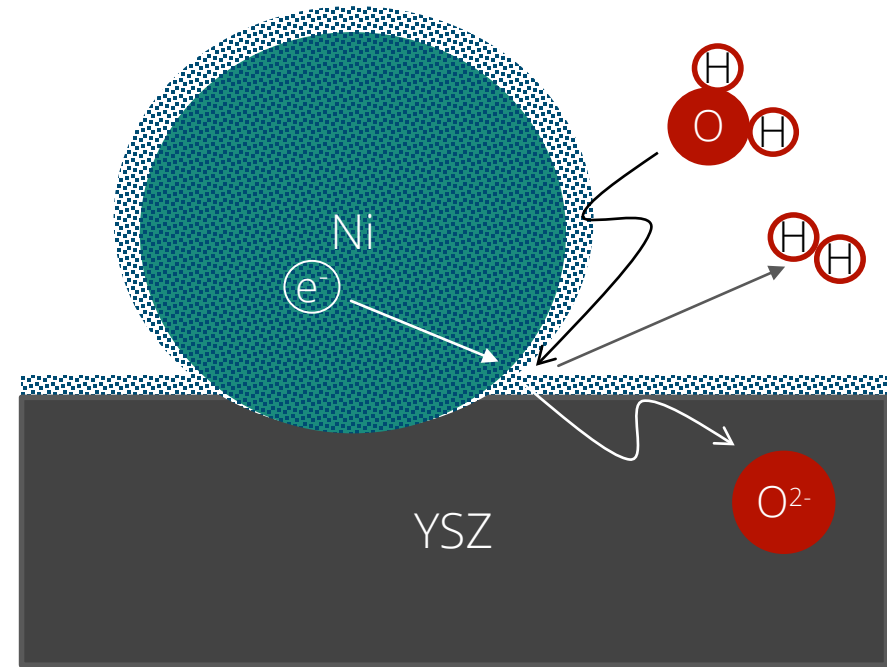
- ❖ Outlook: Develop robust electrode preventing Ni migration
- ❖ Challenge: Binding Ni in complex electrode microstructure while preserving TPB density
- ❖ Solution: Conformal ALD coating of chemical anchor compatible with SOC manufacturing

# Advantage of Anchoring

- Prevents Ni migration and agglomeration while preserving Ni for TPBs
- Minimized risk of blocking TPB



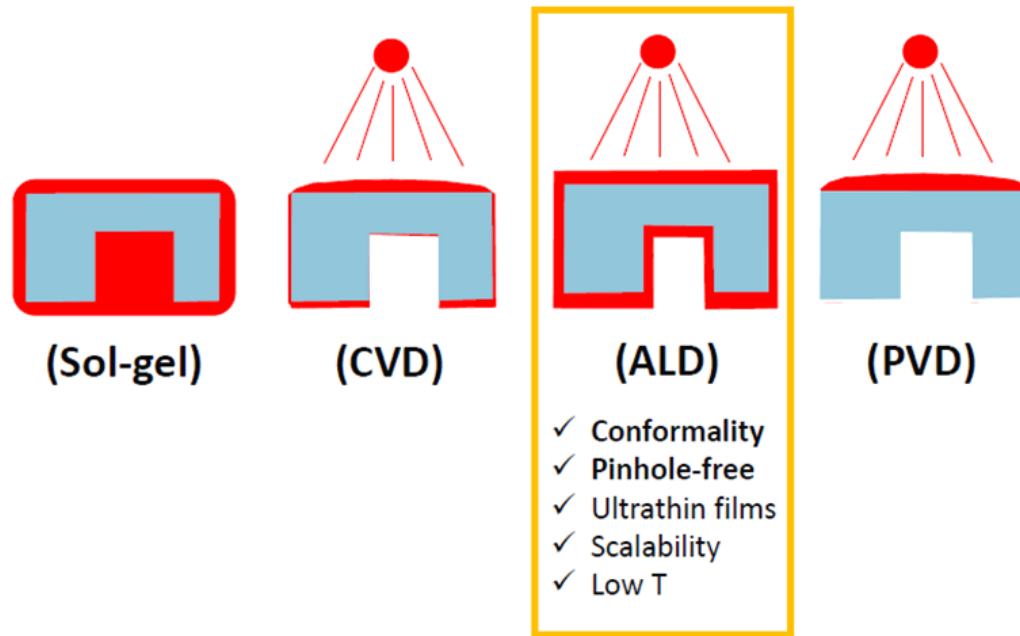
Anchoring



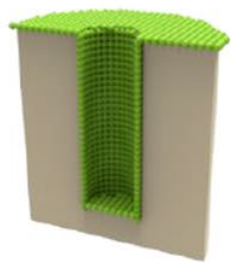
Porous overcoat

# Atomic Layer Deposition (ALD)

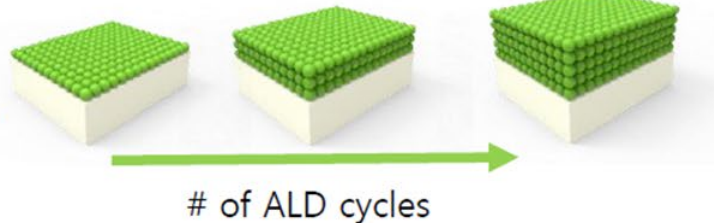
## Thin film coating methods



- ALD is driven by surface chemistry
- Requires unique chemical precursors
- Requires careful design of ALD systems



Good conformality

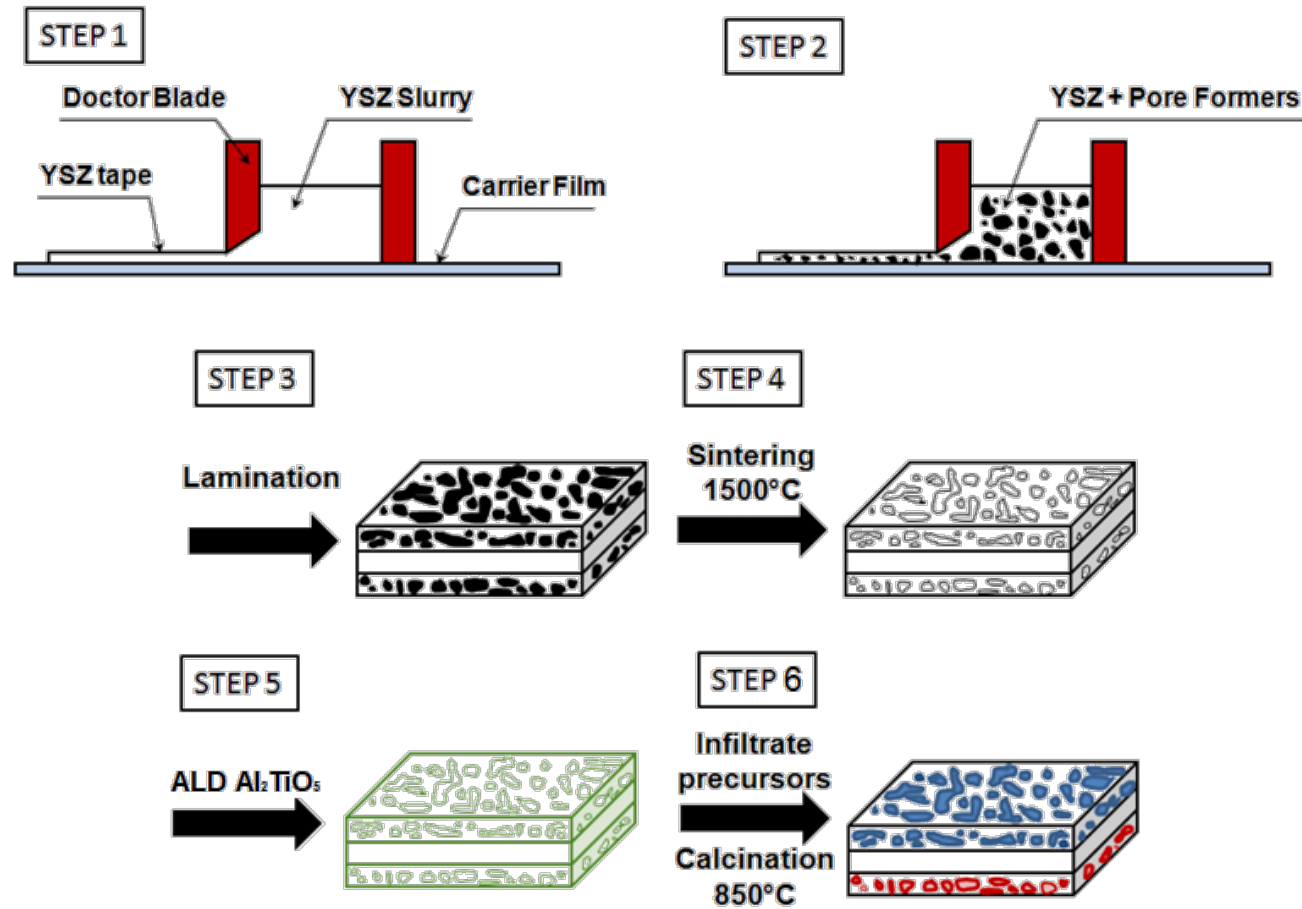


Thickness control



Good uniformity

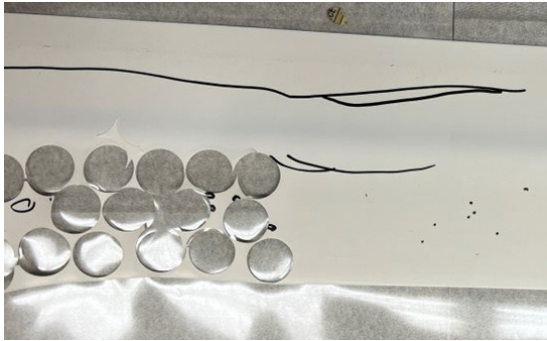
# Approach



- Cells fabricated via tape casting
- $\text{Al}_2\text{TiO}_5$  anchor will be deposited by ALD into the cell scaffold
- Wet infiltration to add the active components
- Calcination anneal will activate anchor

# Cell Fabrication – Tape Casting

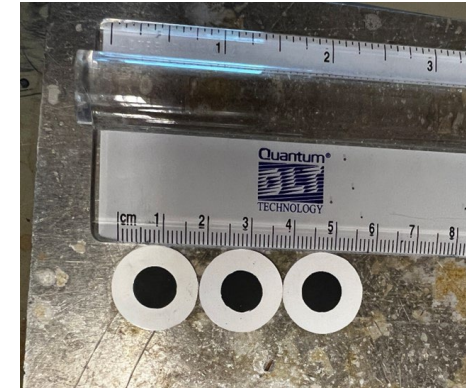
- Cells are fabricated using tape casting with a slurry containing YSZ or YSZ plus graphite pore formers



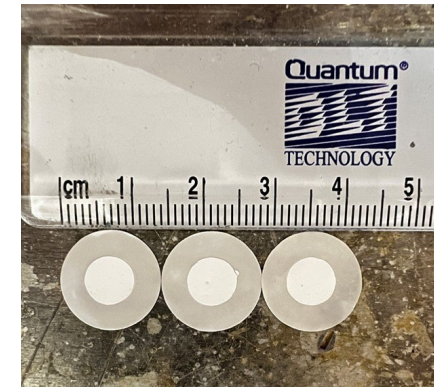
YSZ tape used for making dense electrolyte layer



YSZ tape with graphite pore former used for making electrode layers



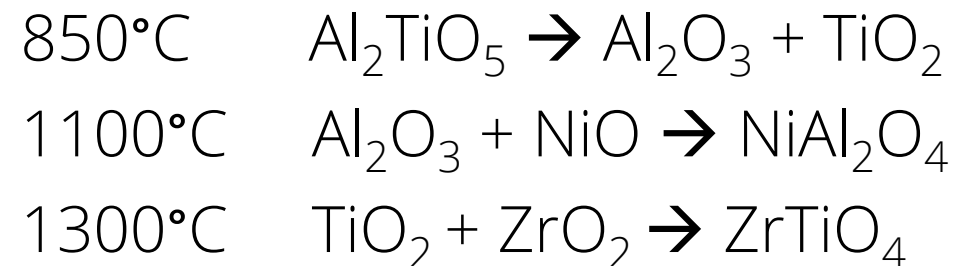
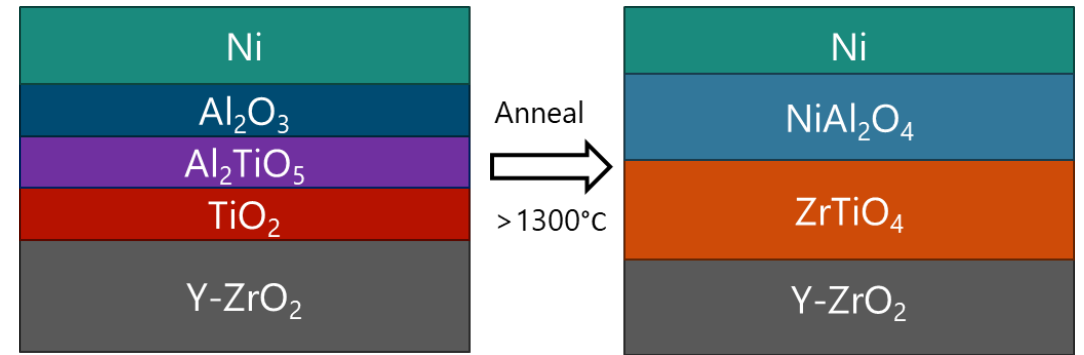
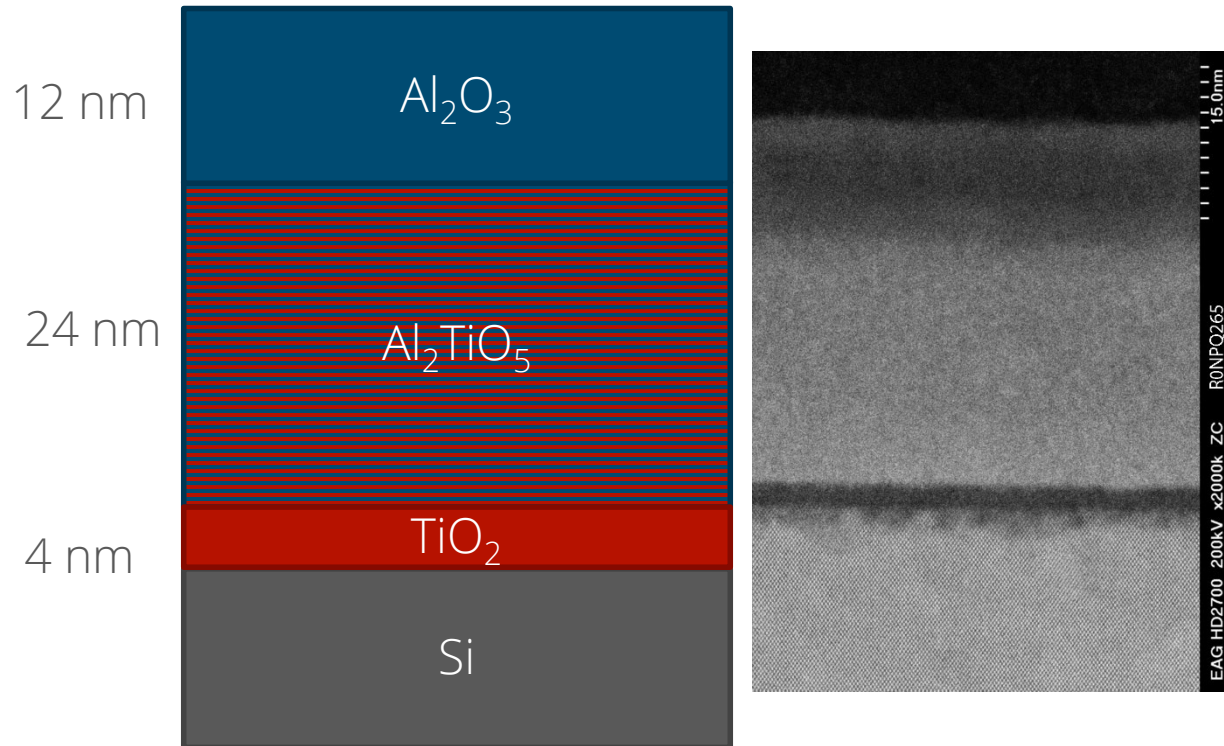
Cells before sintering



Cells after sintering 1500°C



# Initial Anchor ALD Process Development

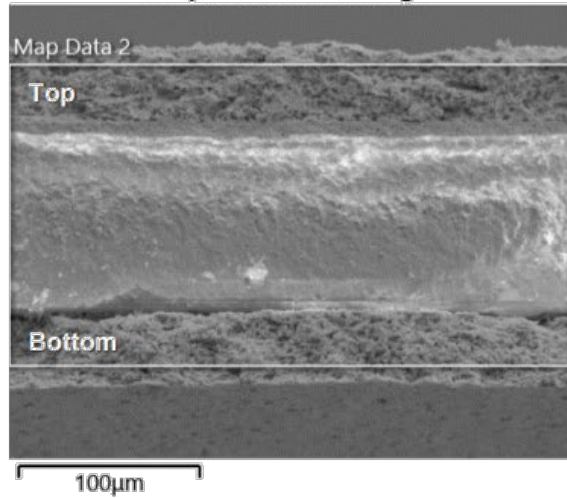


\* SEM image is of film deposited on flat Si wafer substrates at same time as infiltration into cell

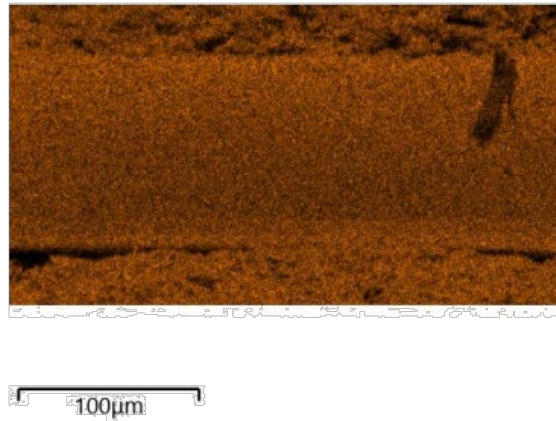
# Elemental Mapping of Anchor in Button Cell

Accelerating voltage = 20 kV

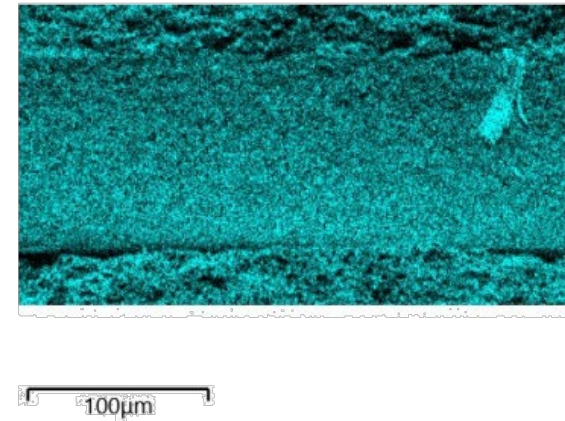
Map 2 Electron Image



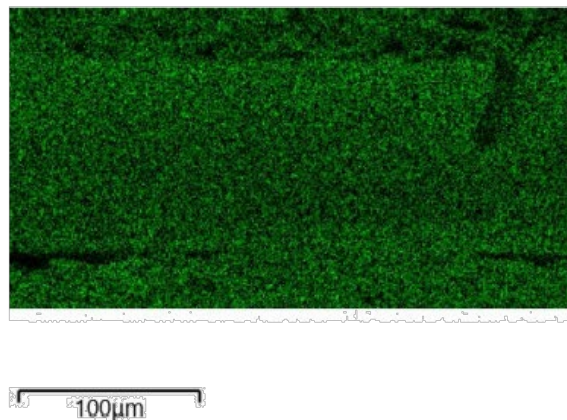
Zr L series



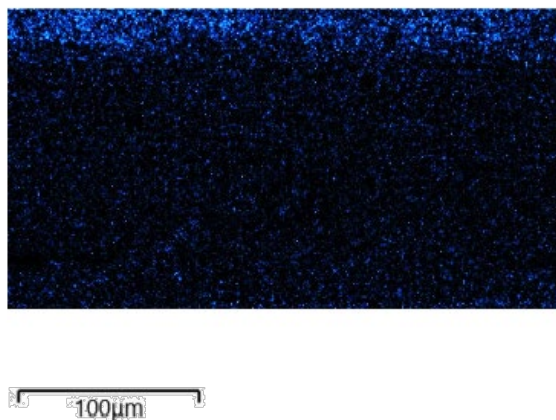
O K series



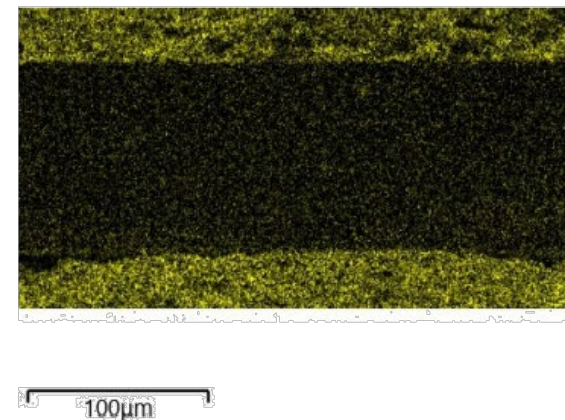
Y L series



Ti K series



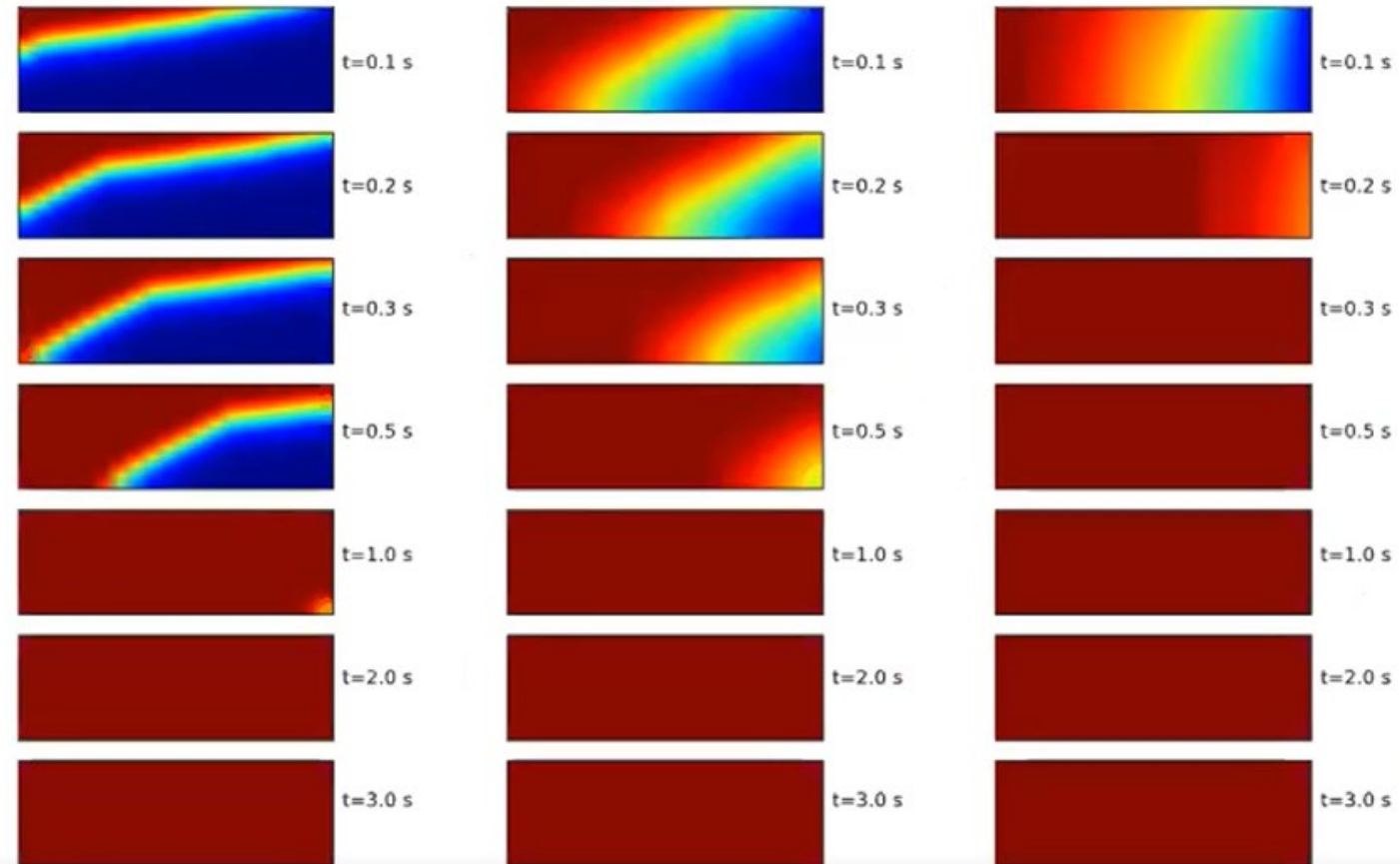
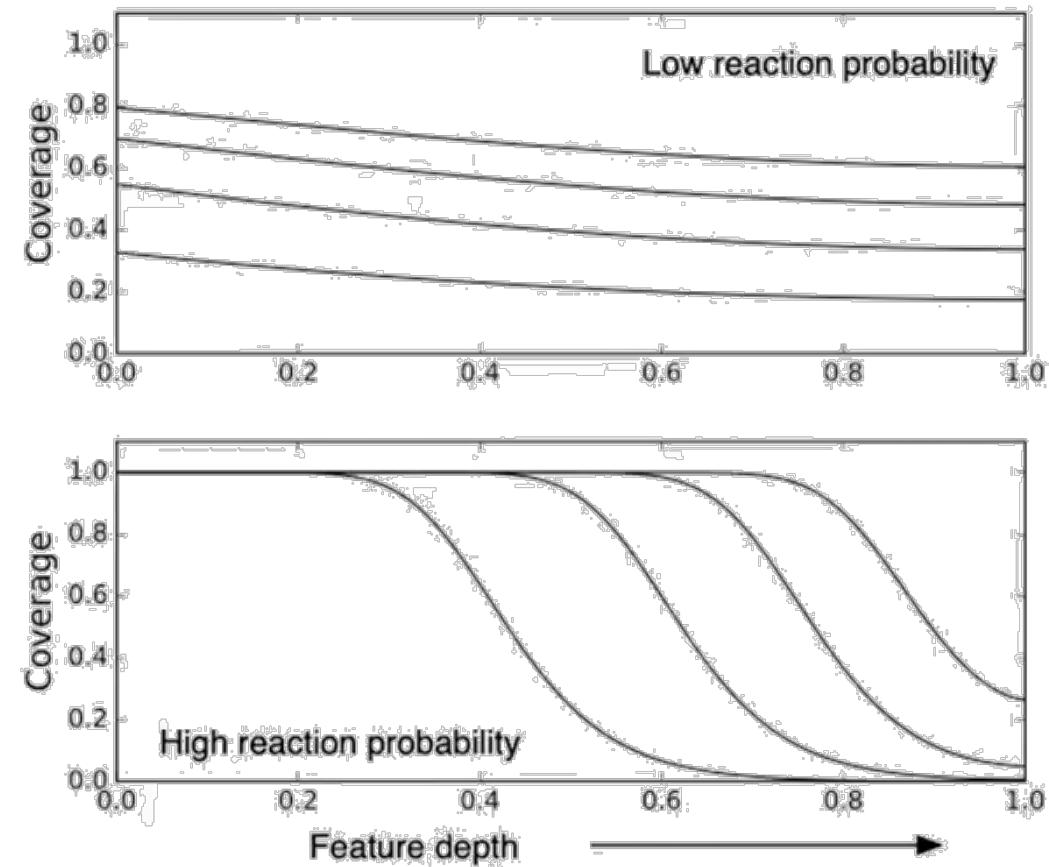
Al K series



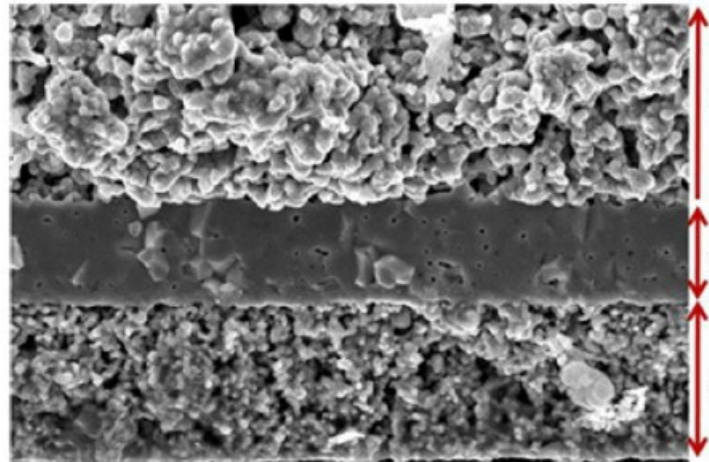
# ALD in Porous Materials

High Aspect Ratio Substrate

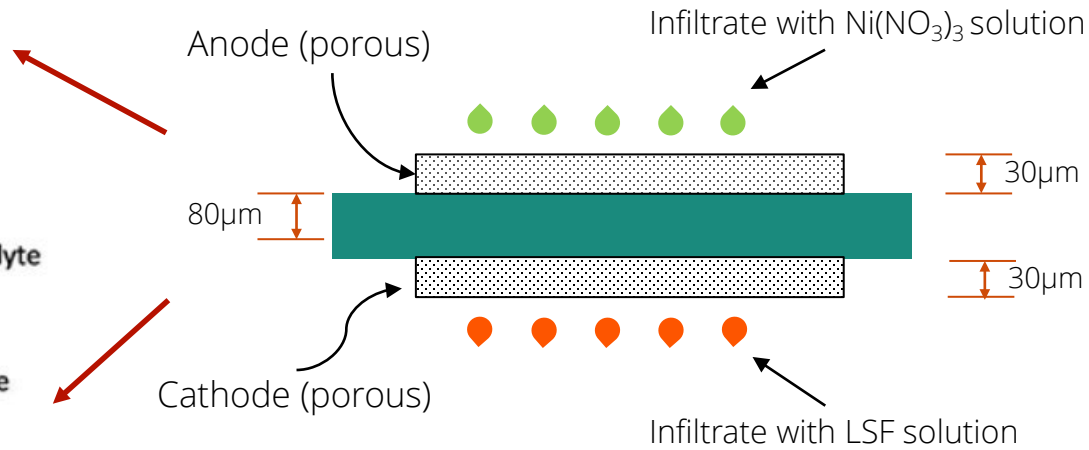
Decreasing sticking probability →



# Cell Fabrication: Electrode Infiltration – Post ALD



Cross-section micrograph showing a typical cell structure



Anode infiltrated with  $\text{Ni}(\text{NO}_3)_3$  solution and heated to  $1300\text{ }^\circ\text{C}$



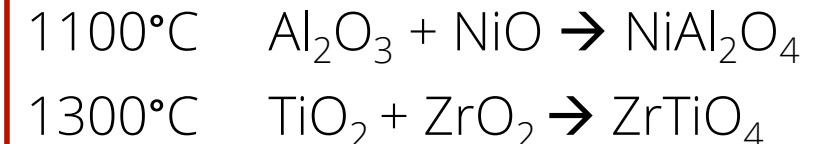
Cathode infiltrated with LSF solution followed by drying.

# Further testing with cells coated by ALD

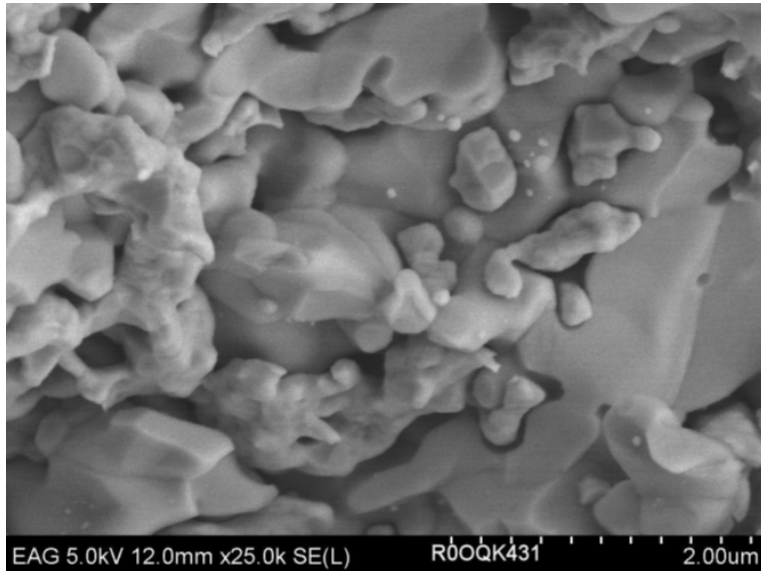
- Calcinate cell at 1400°C for 1 hour (with a ramp rate of 3°C /min) to activate ALT to form  $ZrTiO_4$
- NiO added to anode with 4.5 M  $Ni(NO_3)_2$  solution for 8 cycles. And then calcinate cell at 1100°C for 1 hour (with a ramp rate of 3°C/min) to activate ALT to form  $NiAl_2O_5$
- $La_{0.8}Sr_{0.2}Fe_2O_3$  added to cathode using 15 cycles of wet infiltration. And then calcinate cell to 850°C to form perovskite phase
- Infiltrate another 7 cycles of  $Ni(NO_3)_2$  solution to load the same amount of Ni on the anode as the uncoated cell (total 15 infiltrations)
- Complete cell and test by measuring performance at 700°C, heating to 800°C for 1 hour, re-testing at 700°C, then heating to 900°C for 1 hour, and re-testing at 900°C



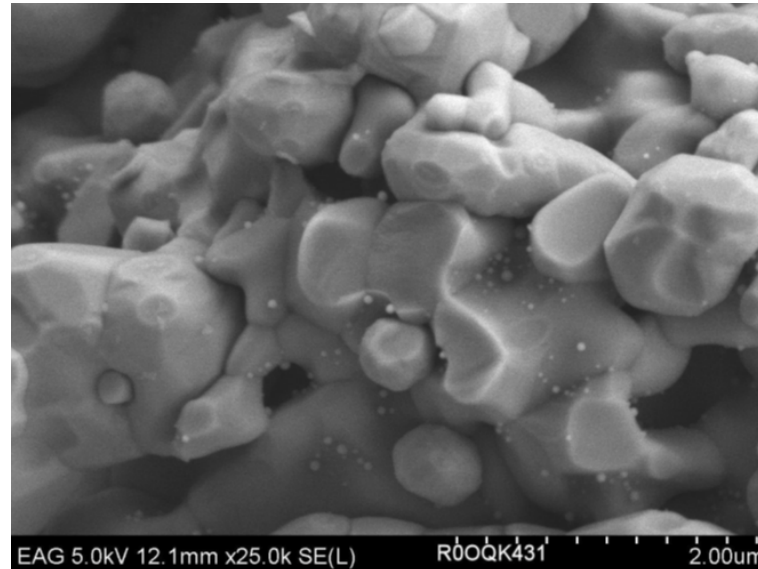
*Cell infiltrated by  $Ni(NO_3)_3$  on the anode side and heated up to 1100 °C*



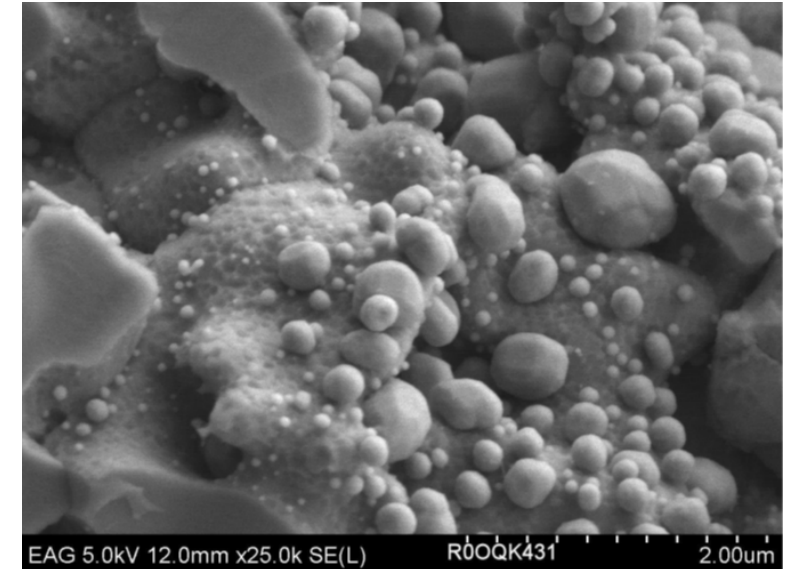
# SEM Cross-Section of Electrode Before and After Stressing



Before Stressing

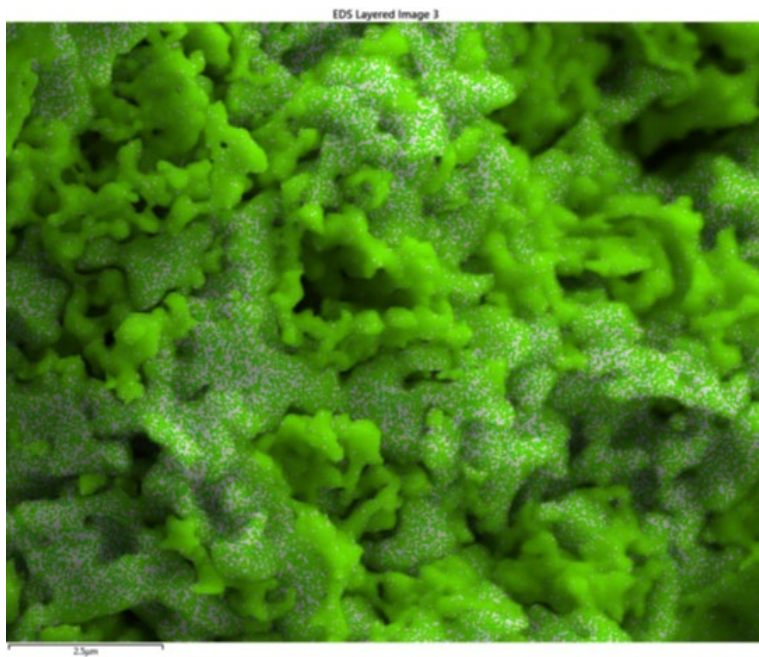


Without ALD coating



With ALD coating

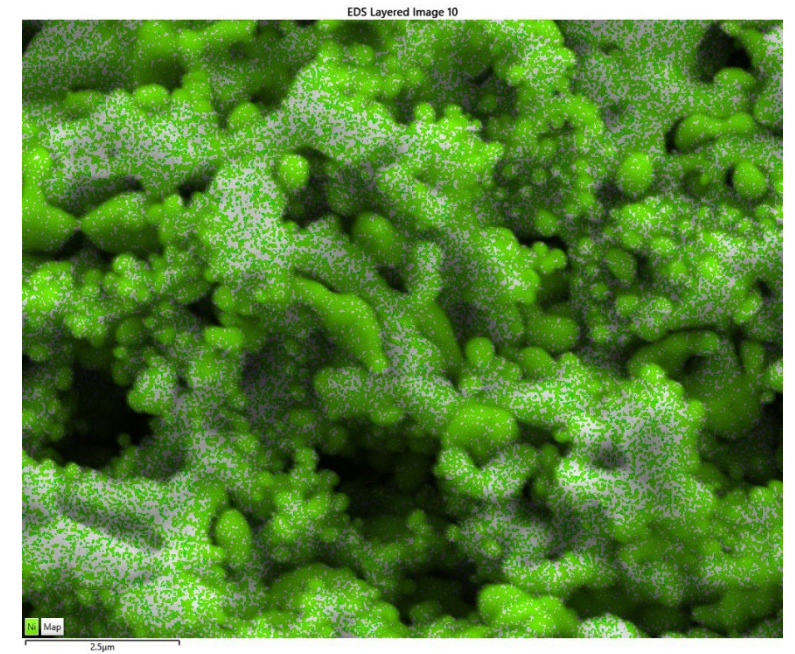
# Addition of Ni EDS Overlay



Before Stressing

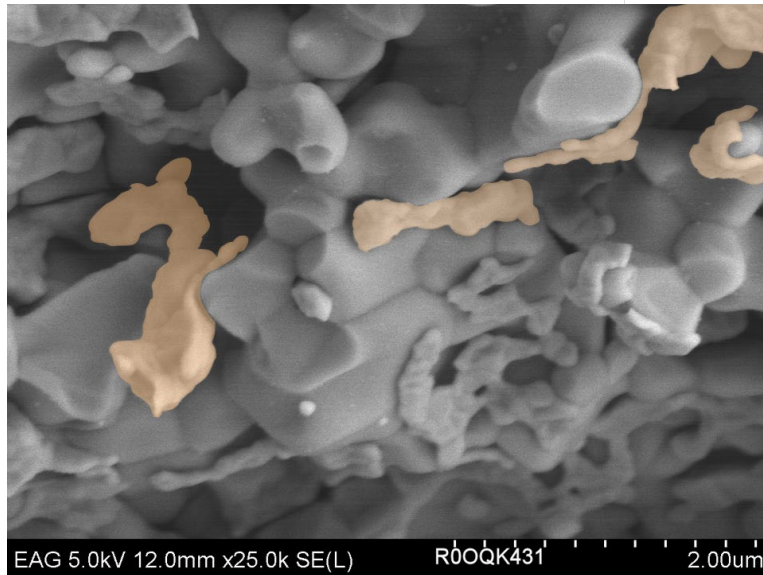
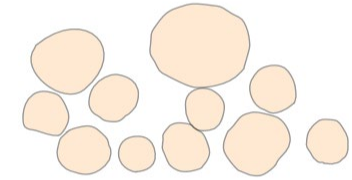
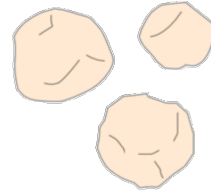
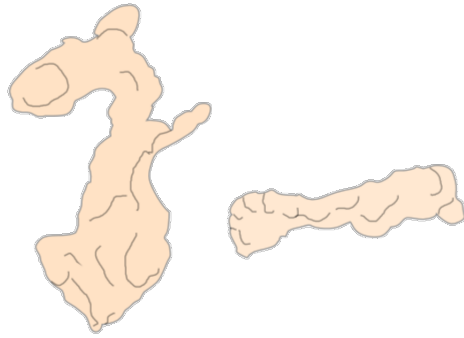


Without ALD coating

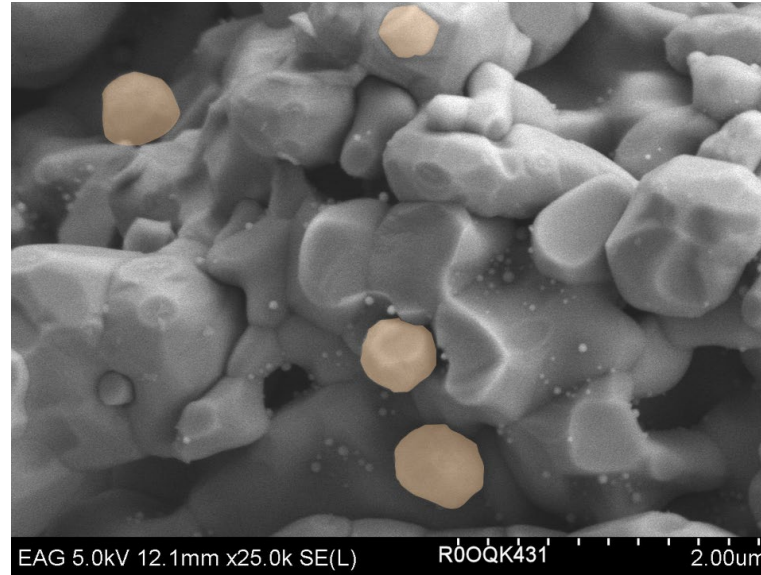


With ALD coating

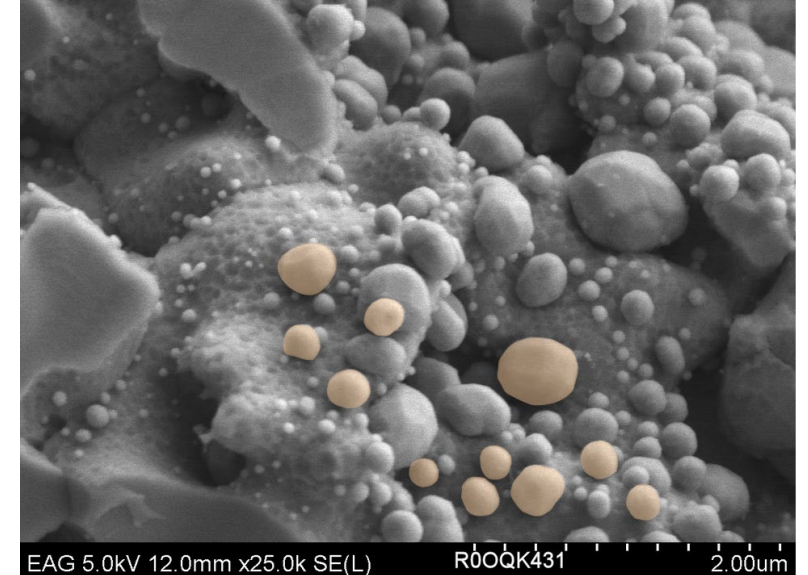
# Ni in the Electrode Before and After Stressing



Before Stressing



Without ALD coating

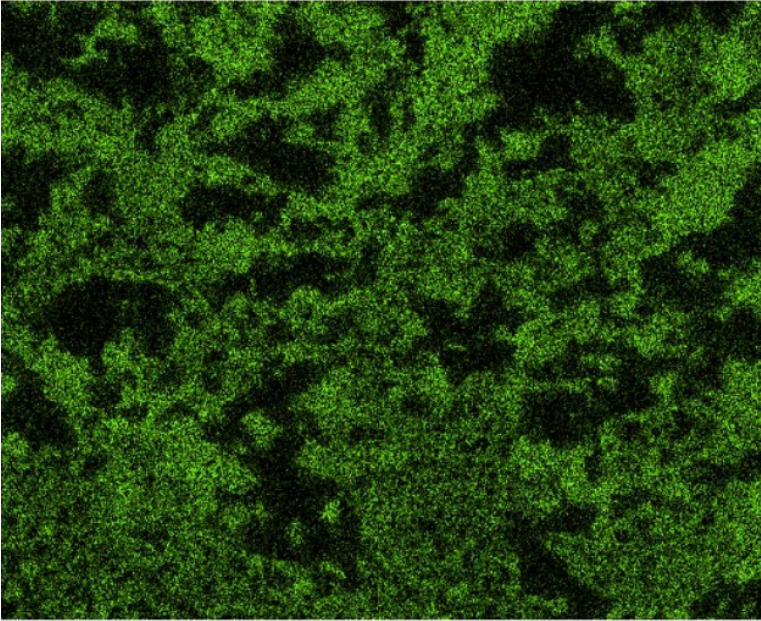


With ALD coating



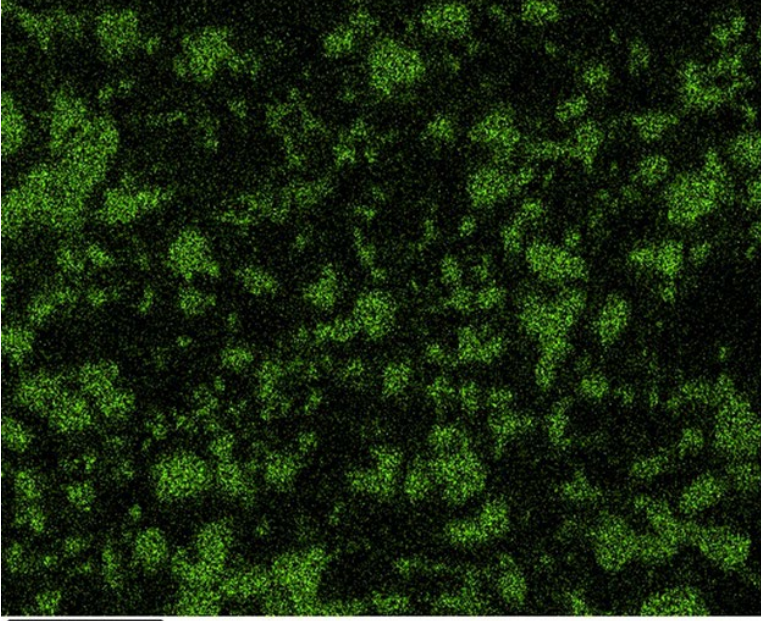
# And At the Macro Level

Ni K series



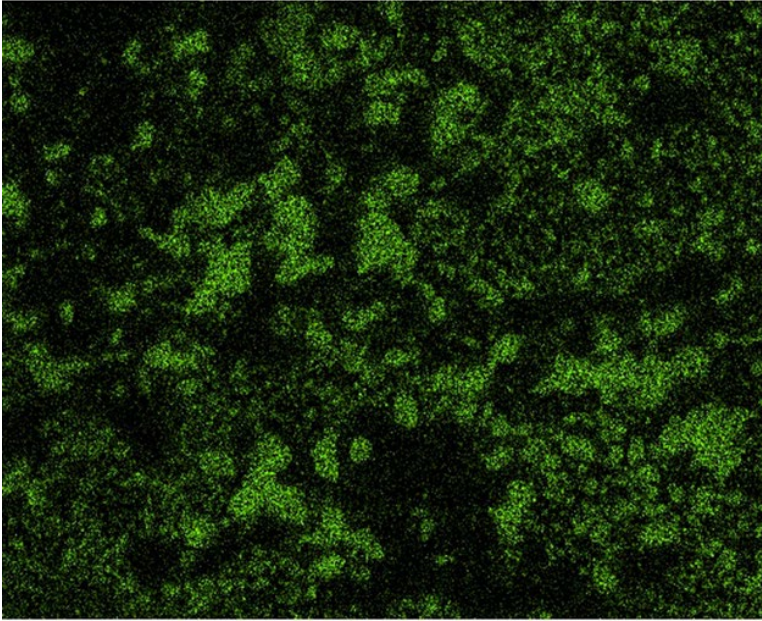
Before Stressing

Ni K series



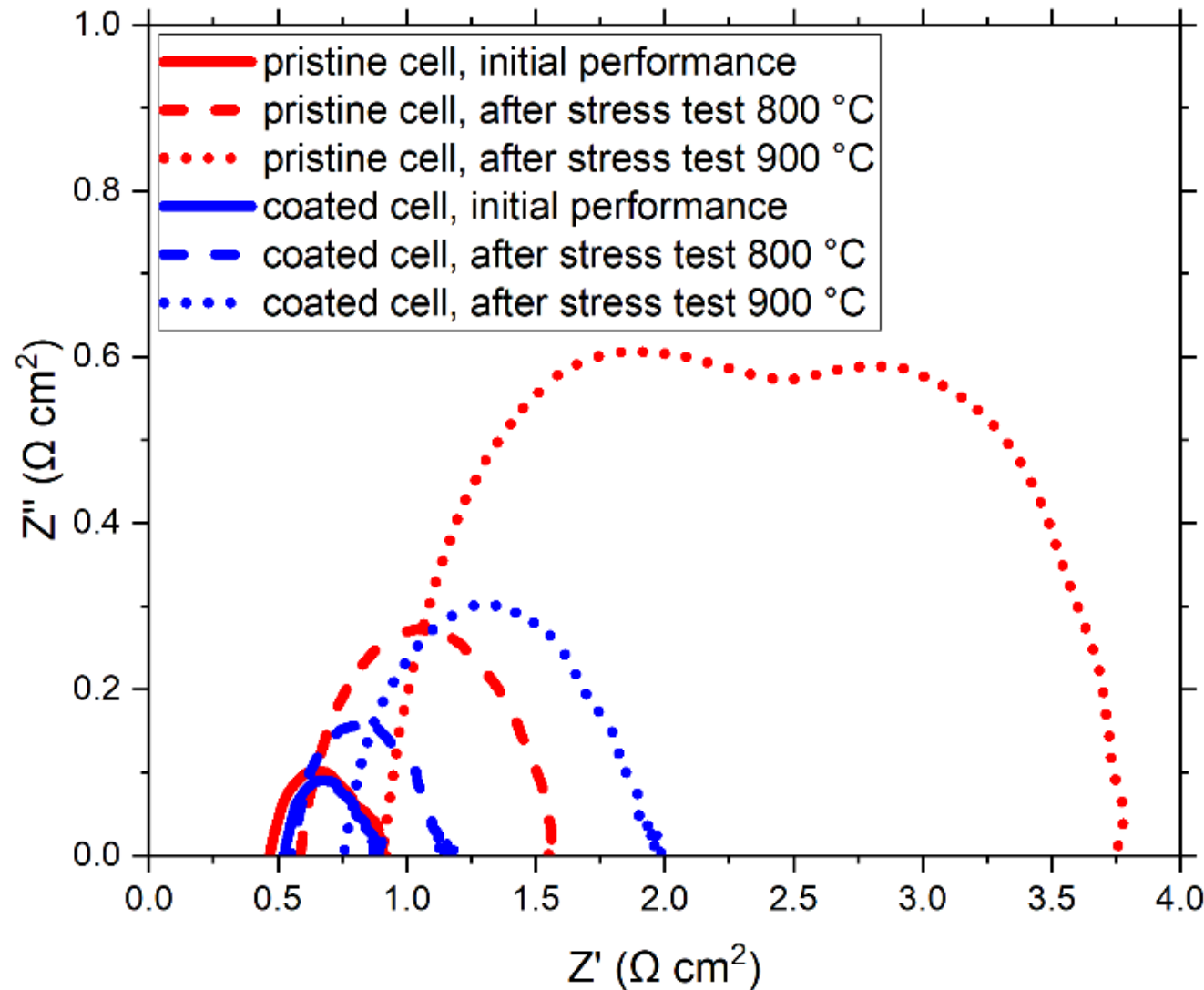
Without ALD coating

Ni K series



With ALD coating

# Electrochemical Impedance Spectra Confirmation

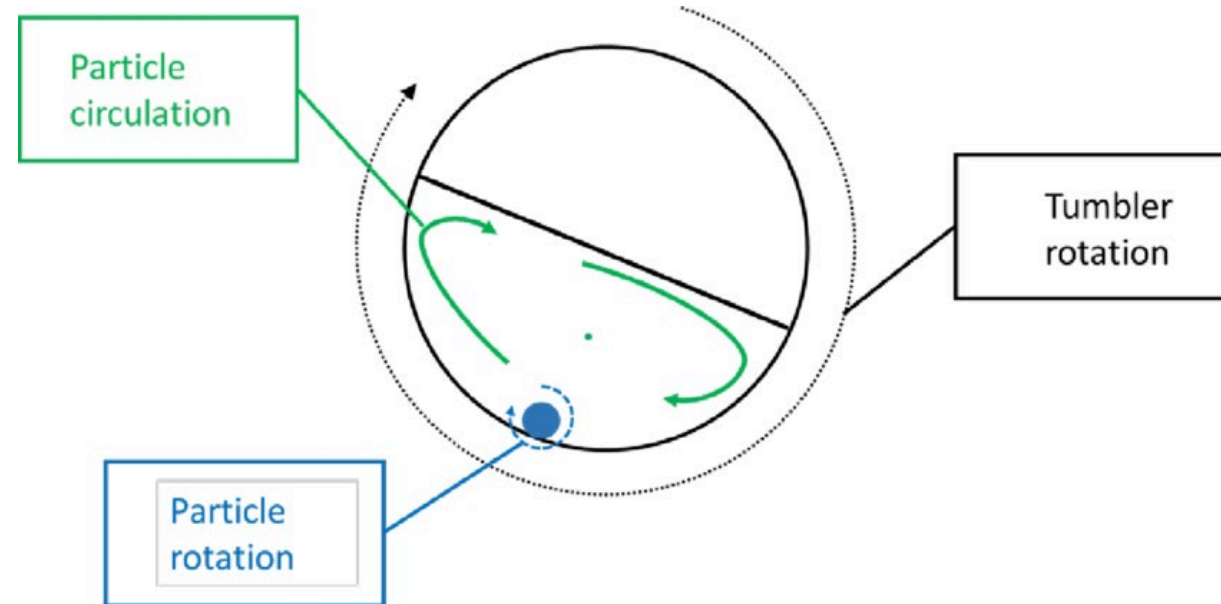
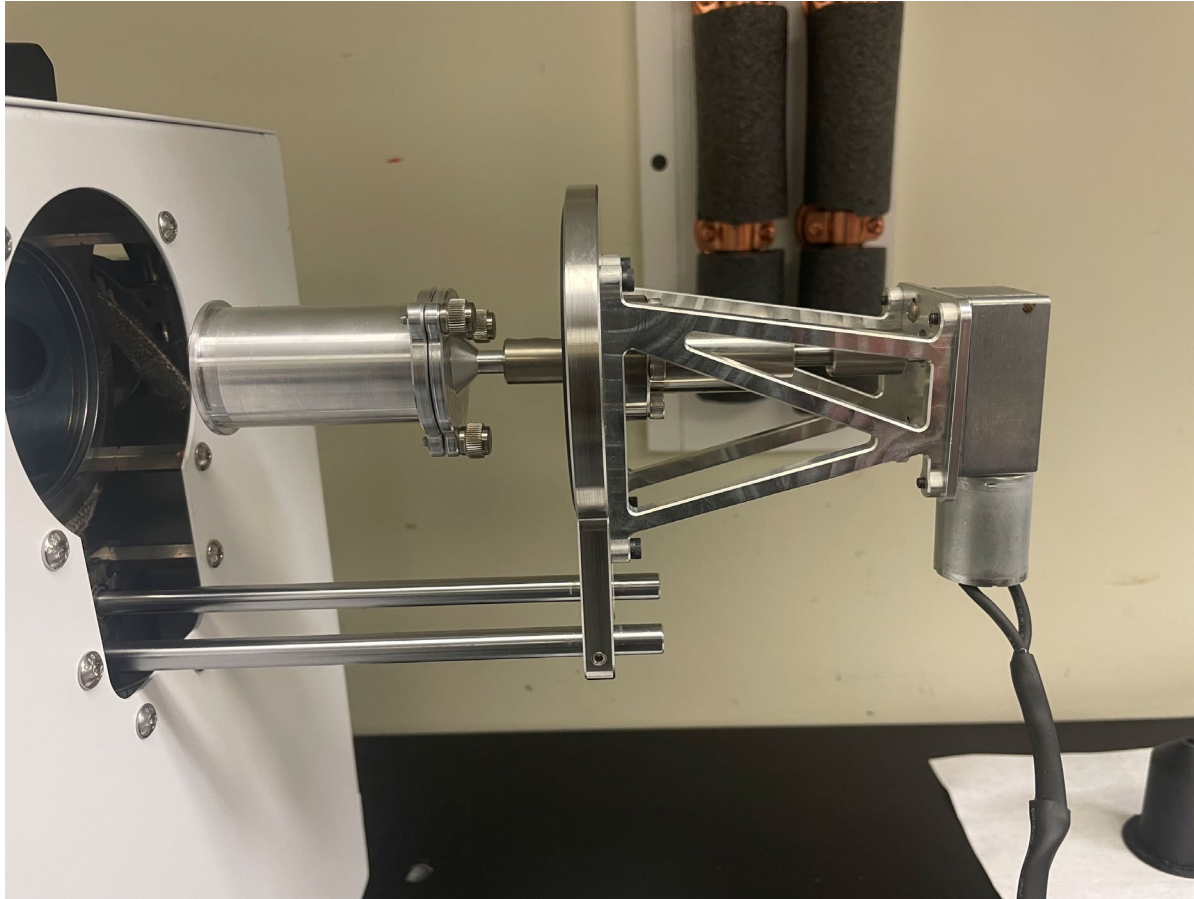


Cells were tested in fuel-cell mode using humidified  $\text{H}_2$  (3%  $\text{H}_2\text{O}$ )

# Next Steps

1. Optimize and demonstrate the repeatability of the anchoring by ALT in Ni-YSZ button cells ensuring
  - a) A process in which all the nickel is properly anchored,
  - b) 5 identical cells show the same performance preventing nickel migration and agglomeration
2. Develop and validate the performance of ALD within current SOEC manufacturing

# Particle ALD for Scale Up



As the tumbler rotates, the powder material circulates, and individual particles rotate exposing all surfaces for even ALD coating

# Conclusion

- We developed an ALD process for depositing ALT conformally on high aspect ratio surfaces
- We successfully demonstrated that a thin ALT anchor coating deposited by ALD significantly enhances the thermal stability of Ni in an infiltrated Ni-YSZ electrode button cell and have on-going experiments to further validate the results
- We are working with SOEC manufacture OxEon Energy to evaluate scale up through a method compatible with current processing



# Acknowledgements



Program Managers Debalina Dasgupta and John Homer



Collaborators Prof. John Vohs (UPENN), Zhouming Feng (UPENN),  
Dr. Jenna Pike (OxEon) and Dr. Elango Elangovan (OxEon)